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First Call for Papers

2014 International Conference on Simulation of
Semiconductor Processes and Devices

SISPAD2014

September 9 – 11, 2014

Workshop, September 8

Mielparque Yokohama, Yokohama, JAPAN

Co-sponsored by Japan Society of Applied Physics

Technical co-sponsored by IEEE Electron Devices Society



Scope:

This conference provides an opportunity for the presentation and discussion of the latest advances in modeling and simulation of semiconductor devices, processes, and equipment for integrated circuits.

Topics:

- Modeling and simulation of all sorts of semiconductor devices, including FinFETs, ultra-thin SOI devices, emerging memory devices, optoelectronic devices, TFTs, sensors, power electronic device, widegap semiconductor devices, spintronic devices, tunnel FETs, SETs, carbon-based nanodevices, organic electronic devices, and bioelectronic devices
- Modeling and simulation of all sorts of semiconductor processes, including first-principles material design and growth simulation of nano-scale fabrication
- Fundamental aspects of device modeling and simulation, including quantum transport, thermal transport, fluctuation, noise, and reliability
- Compact modeling for circuit simulation, including low-power, high frequency, and power electronics applications
- Process/device/circuit co-simulation in context with system design and verification
- Equipment, topography, lithography modeling
- Interconnect modeling, including noise and parasitic effects
- Numerical methods and algorithms, including grid generation, user-interface, and visualization
- Metrology for the modeling of semiconductor devices and processes

Abstract Submission:

Authors are invited to submit a two-page abstract (A4 size or 22×28 cm) including figures. Full submission information will be updated in the Second Call for Papers and the following web site.

<https://sites.google.com/site/sispad2014/>

Authors of accepted papers will be notified by May 15, 2014. Camera-ready copy of a four-page manuscript will be required from the authors for inclusion in the Conference Proceedings by June 30, 2014.

Deadline for submission of abstract: March 31, 2014

Any inquiries on submission should be sent to:

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